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2015 Joint International EUROSIO Workshop and International Conference on Ultimate Integration on Silicon

Session I: Nanowires and nanosensors

Nano systems and nano scaled devices for new applications in biology and nanotechnology (invited)

D. Collard (LIMMS/CNRS-IIS, UTokyo - Japan) p. 1

From Double to Triple Gate: Modeling Junctionless Nanowire Transistors

B. C. Paz, M. Casse, S. Barraud, F. Avila-Herrera, A. Cerdeira, G. Reimbold, O. Faynot, M. A. Pavanello p. 5

350K Operating Silicon Nanowire Single Electron/Hole Transistors Scaled Down to 3.4nm Diameter and 10nm Gate Length

R. Lavieville, S. Barraud, A. Corna, X. Jehl, M. Sanquer, and M. Vinet p. 9

P-type Trigate Nanowires: Impact of Nanowire Thickness and $\text{Si}_{0.7}\text{Ge}_{0.3}$ Source-Drain Epitaxy

L. Gaben, S. Barraud, M.-P. Samson, J.-M. Hartmann, C. Vizios, F. Aussenac, F. Allain, S. Monfray, F. Boeuf, T. Skotnicki, F. Balestra, M. Vinet p. 13

Effect of Independently Sized Gates on the Delay of Reconfigurable Silicon Nanowire Transistor Based Circuits

J. Trommer, A. Heinzig, T. Baldauf, S. Slesazeck, T. Mikolajick, W.M. Weber p. 17

Session II: Power devices and ESD protection

A Model for Hot-Carrier Degradation in nLDMOS Transistors Based on the Exact Solution of the Boltzmann Transport Equation Versus the Drift-Diffusion Scheme

P. Sharma, S. Tyaginov, Y. Wimmer, F. Rudolf, H. Enichlmair, J.-M. Park, H. Ceric, and T. Grasser p.21

Leakage current and breakdown of GaN-on-Silicon vertical structures

D. Cornigli, F. Monti, S. Reggiani, E. Gnani, A. Gnudi, G. Baccarani p.25

BIMOS transistor in thin silicon film and new solutions for ESD protection in FDSOI UTBB CMOS technology

Ph. Galy, S. Athanasiou, S. Cristoloveanu p.29

A new Latch-free LIGBT on SOI

J. Olsson, L. Vestling, K.-H. Eklund p.33

Session III: FDSOI devices

Fully depleted SOI: achievements and future developments (invited)

M. Haond (STMicroelectronics - France) p.37

Self-Heating in 28 nm Bulk and FDSOI

S. Makovejev, N. Planes, M. Haond, D. Flandre, J.-P. Raskin, V. Kilchytska p.41

Impact of Non Uniform Strain configuration on transport properties for FD14+ devices

C. Medina-Bailon, C. Sampedro, F. Gamiz, A. Godoy, L. Donetti p.45

Modeling study of the mobility in FDSOI devices with a focus on near-spacer-region

F.G.Pereira, D.Rideau, O.Nier, C. Tavernier, F.Trioizon, D.Garetto, G.Mugny, B.Sklenard, G.Hiblot, M.Pala p.49

Session IV: Steep-slope devices - I

CMOS-compatible abrupt switches based on VO2 metal-insulator transition

W. A. Vitale, C. F. Moldovan, A. Paone, A. Schueler, A. M. Ionescu p.53

Effects of Dit-induced degradation on InGaAs/InAlAs Nanowire Superlattice-FET using Al₂O₃ and HfO₂/La₂O₃ as gate stacks

P. Maiorano, E. Gnani, A. Gnudi, S. Reggiani, G. Baccarani p.57

Fabrication and Analysis of Vertical p-type InAs-Si Nanowire Tunnel FETs

D. Cutaia, K. E. Moselund, M. Borg, H. Schmid, L. Gignac, C.M. Breslin, S. Karg, E. Uccelli, P. Nirmalraj H. Riel p.61

Strained Si Nanowire GAA n-TFETs for low supply voltages

G. V. Luong, S. Trellenkamp, K. K. Bourdelle, Q. T. Zhao and S. Mantl p.65

Experimental Investigations of SiGe Channels for Enhancing the SGOI Tunnel FETs Performance

C. Le Royer, A. Villalon, S. Martinie, P. Nguyen, S. Barraud, F. Glowacki, S. Cristoloveanu, M. Vinet p.69

Session V: 2D materials

Investigation of 2D Transition Metal Dichalcogenide Films for Electronic Devices (invited)

G. S. Duesberg, T. Hallam, M. O'Brien, R. Gatensby, H.-Y. Kim, K. Lee, N. C. Berner, N. McEvoy, C. Yim p.73

Spectral sensitivity of a graphene/silicon pn-junction photodetector

S. Riazimehr, D. Schneider, C. Yim, S. Kataria, V. Passi, A. Bablich, G. S. Duesberg, M. C. Lemme p.77

Impact of Hot Carrier Stress on the Defect Density and Mobility in Double-Gated Graphene Field-Effect Transistors

Yu. Yu. Illarionov, M. Walt, A.D. Smith, S. Vaziri, M. Ostling, M.C. Lemme, T. Grasser p.81

Spatial Variability in Large Area Single and Few-layer CVD Graphene

C. F. Moldovan, K. Gajewski, M. Tamagnone, R. S. Weatherup, H. Sugime, A. Szumska, W. A. Vitale, J. Robertson, A. M. Ionescu p.85

Relevance of the physics of off-plane transport through 2D materials on the design of vertical transistors

G. Iannaccone, Q. Zhang, S. Bruzzone, G. Fiori p.89

Towards Amplifier Design with a SiC Graphene Field-Effect Transistor

J. D. Aguirre-Morales, S. Fregonese, M. S. Khenissa, M.M. Belhaj, A. D. D. Dwivedi, H. Happy, T. Zimmer p.93

Session VI: III-V materials and devices

Tri-gate In_{0.53}Ga_{0.47}As-on-insulator Junctionless Field Effect Transistors

V. Djara, L. Czornomaz, N. Daix, D. Caimi, V. Deshpande, E. Uccelli, M. Sousa, C. Marchiori, J. Fompeyrine p.97

Modeling approaches for band-structure calculation in III-V FET quantum wells

E. Caruso, G. Zerveas, G. Baccarani, L. Czornomaz, N. Daix, D. Esseni, E. Gnani, A. Gnudi, R. Grassi, M. Luisier, T. Markussen, P. Palestri, A. Schenk, L. Selmi, M. Sousa, K. Stokbro, M. Visciarelli p.101

Investigation of Performance Limiting Factors of sub-10nm III-V FinFETs

P. Feng, S. Narayanan, E. Towie, C. Alexander, S. M. Amoroso, A. Asenov, S. M. Pandey, B. Sahu, F. Benistant .. p.105

Drift-Diffusion Simulation Without Einstein Relation

F. M. Bufler, A. Erlebach, and A. Wettstein p.109

Al₂O₃/InGaAs interface study on MOS capacitors for a 300mm process integration

M. Billaud, J. Duvernay, H. Grampeix, B. Pelissier, M. Martin, T. Baron, H. Boutry, Z. Chalupa, M. Cassé, T. Ernst, M. Vinet p.113

On the enhancement of electron mobility in ultra-thin (111)-oriented In_{0.53}Ga_{0.47}As channels

M. Poljak, S. Krivec, T. Suligoj p.117

Session VII: Memories and magnetic devices

Low-power 3D integrated ferromagnetic computing (invited)

M. Becherer, S. Breikreutz, I. Eichwald, G. Ziemys, J. Kiermaier, G. Csaba, D. Schmitt-Landsiedel p.121

Modeling of OxRAM Variability from Low to High Resistance State using a Stochastic Trap Assisted Tunneling-based Resistor Network

D. Garbin, Q. Rafhay, E. Vianello, S. Jeannot, P. Candelier, B. DeSalvo, G. Ghibaudo, L. Perniola p.125

Schottky barrier height engineering for next generation DRAM capacitors

K. Cho, M. Pesic, S. Knebel, C. Jung, J. Chang, H. Lim, N. Kolomiets, V. V. Afanas, U. Schroeder, T. Mikolajick p.129

A new high resolution Random Telegraph Noise (RTN) characterization method for Resistive RAM

M. Maestro, J. Diaz, A. Crespo-Yepes, M. B. Gonzalez, J. Martin-Martinez, R. Rodriguez, M. Nafria, F. Campabadal, X. Aymerich p.133

Session VIII: Steep-slope devices - II

Effects of electrical stress and ionizing radiation on Si-based TFETs

L. Ding, E. Gnani, S. Gerardin, M. Bagatin, F. Driussi, L. Selmi, C. Le Royer, A. Paccagnella p.137

Efficient Quantum Mechanical Simulation of Band-to-band Tunneling

C. Alper, P. Palestri, J. L. Padilla, A. Gnudi, R. Grassi, E. Gnani, M. Luisier, A. M. Ionescu p.141

Investigation of Ambipolar Signature in SiGeOI Homo Junction Tunnel FETs

R. P. Oeflein, L. Hutin, J. Borrel, A. Villalon, C. Le Royer, S. Martinie, C. Tabone, M. Vinet p.145

Study of Low Frequency Noise in Vertical NW-Tunnel FETs with Different Source Compositions

F. S. Neves, P. G. D. Agopian, J. A. Martino, B. Cretu, A. Vandooren, R. Rooyackers, E. Simoen, A. Thean and C. Claeys p.149

New Insights in Z²-FET Mechanisms at Variable Temperature

H. El Dirani, L. Onestas, P. Ferrari, Y. Solaro, P. Fonteneau, S. Cristoloveanu p.153

Session IX: Advanced integration technologies

GeSn for nanoelectronic and optical applications (invited)

D. Buca, S. Wirths, D. Stange, N. von den Driesch, T. Stoica, D. Grützmacher, S. Mantl, Z. Ikonc, J.-M. Hartmann p.157

Mobility improvement of ultrathin-body Germanium-on-insulator (GeOI) MOSFETs on flipped Smart-Cut™ GeOI substrates

X. Yu, J. Kang, R. Zhang, M. Takenaka, and S. Takagi p.161

Characterization of bonding surface and electrical insulation properties of inter layer dielectrics for 3D monolithic integration

K. Garidis, G. Jayakumar, A. Asadollahi, E. Dentoni Litta, P.-E. Hellstrom, M. Ostling p.165

Study of High-Temperature Smart Cut™: Application to Thin Films of Single Crystal Silicon and Silicon-On-Sapphire Films

R. Meyer, O. Kononchuk, H. Moriceau, M. Lemiti, M. Bruel p.169

Reverse terrace graded Si_{1-x}Ge_x/Ge/Si(001) virtual substrates grown using RP-CVD on on-axis and 6 degree off-axis substrates for future developments in III-V materials integration

V. Sivadasan, M. Myronov, S. Rhead, J. Halpin, D. Leadley p.173

New Insights on Strained-Si On Insulator Fabrication by Top Recrystallization of Amorphized SiGe on SOI

A. Bonneville, S. Reboh, L. Grenouillet, C. Le Royer, Y. Morand, S. Maitrejean, J.-M. Hartmann, A. Halimaoui, D. Rouchon, M. Cassé, C. Plantier, R. Wacquez, M. Vinet p.177

Session X: Advanced characterization techniques

Low frequency noise statistical characterization of 14nm FDSOI technology node

E. G. Ioannidis, C. G. Theodorou, S. Haendler, M.-K. Joo, E. Josse, C. A. Dimitriadis, G. Ghibaud p.181

Second Harmonic Generation for non-destructive characterization of silicon-on-insulator substrates

I. Ionica, L. Pirro, V. Nguyen, J. Changala, M. Kryger A. Kaminski, G. Vitrant, L. Onestas, S. Cristoloveanu p.185

Thickness Characterization by Capacitance Derivative in FDSOI p-i-n Gated Diodes

C. Navarro, M. Bawedin, F. Andrieu, J. Cluzel, Y. Solaro, P. Fonteneau, F. Martinez, B. Sagnes, S. Cristoloveanu p.189

Measurement of the Minimum Energy Point in Silicon on Thin-BOX(SOTB) and Bulk MOSFET

S. Nakamura, J. Kawasaki, Y. Kumagai, K. Usami p.193

Characterization of Flexible CMOS Technology Transferred onto a Metallic Foil

J. Philippe, A. Lecavelier des Etangs-Levallois, P. Latzel, F. Danneville, J.-F. Robillard, D. Gloria, E. Dubois p.197

Poster Session

Electron relaxation times and resistivity in metallic nanowires due to tilted grain boundary planes

K. Moors, B. Soree, Z. Tokei, W. Magnus p.201

Simulation of the Measurement by Scanning Electron Microscopy of Edge and Linewidth Roughness Parameters in Nanostructures

M. Ciappa, E. Ilgusatiroglu, A. Yu. Illarionov p.205

TFET/CMOS Hybrid Pseudo Dual-Port SRAM for Scratchpad Applications

N. Gupta, A. Makosiej, O. Thomas, A. Amara, A. Vladimirescu, C. Anghel p.209

Analytical Approach to Consider Gaussian Junction Profiles in Compact Models of Tunnel-FETs

M. Graef, F. Hain, F. Hosenfeld, B. Iniguez, A. Kloes p.213

Toward understanding of donor-traps-related dispersion phenomena on normally-ON AlGaIn/GaN HEMT through transient simulations

S. Strangio, P. Magnone, F. Crupi, C. Fiegna, C. Pace, G. Iannaccone, A. Heiman, D. Shamir p.217

Power Gating for FDSOI using Dynamically Body-Biased Power Switch

Y. Kumagai, M. Kudo, K. Usami p.221

Disilane and trimethylsilane as precursors for RP-CVD growth of Si_{1-y}C_y epilayers on Si(001)

G. Colston, M. Myronov, S. D. Rhead, D. R. Leadley p.225

A simulation study of short channel effects with a QET model based on Fermi-Dirac statistics for Si, Ge and III-V MOSFETs

S. Sho, S. Odanaka, A. Hiroki p.229

Comparison between vertical silicon NW-TFET and NW-MOSFET from analog point of view

P. G. D. Agopian, J. A. Martino, A. Vandooren, R. Rooyackers, E. Simoen, A. Thean, C. Claeys p.233

Static and low frequency noise characterization in standard and rotated UTBOX nMOSFETs

B. Cretu, E. Simoen, J.-M. Routoure, R. Carin, M. Aoulaiche, C. Claeys p.237

Analytical model of thin-body InGaAs-on-InP MOSFET low-field electron mobility for integration in TCAD tools

G. Betti Beneventi, S. Reggiani, A. Gnudi, E. Gnani, A. Alian, N. Collaert, A. Mokuta, A. Thean, G. Baccarani p.241

Quantum Simulations of a Heterojunction Inter-layer Tunnel FET based on 2-D gapped crystals

J. Cao, M. Pala, A. Cresti, D. Esseni p.245

Quasi-static capacitance measurements in pseudo-MOSFET configuration for Dit extraction in SOI wafers

L. Pirro, I. Ionica, X. Mescot, L. Faraone, S. Cristoloveanu, G. Ghibaudo p.249

Impact of the diameter of vertical Nanowire-Tunnel FETs with Si and SiGe source composition on analog parameters

C. C. M. Bordallo, V. B. Sivieri, J. A. Martino, P. G. D. Agopian, R. Rooyackers, A. Vandooren, E. Simoen, A. Thean, C. Claeys p.253

Cu Nanolines in Coplanar Waveguide Transmission Lines

P. Sarafis, A. G. Nassiopoulou p.257

Enhanced Dynamic Threshold UTBB SOI at High Temperature

K. R. A. Sasaki, M. Aoulaiche, E. Simoen, C. Claeys, J. A. Martino p.261

Improved Analog Operation of Junctionless Nanowire Transistors Using Back Bias

R. Trevisoli, R. T. Doria, M. de Souza, M. A. Pavanello p.265

Nanoscale Characterization of MOS Systems by Microwaves: Dopant Profiling Calibration*L. Michalas, A. Lucibello, C. H. Joseph, E. Brinciotti, F. Kienberger, E. Proietti, R. Marcelli p.269***A Simple Analytical Variable Barrier Transistor Drain Current Model***O. Moldovan, F. Lime, S. Barraud, B. Iniguez p.273***A simple compact model for carrier distribution and its application in single-, double- and triple-gate junctionless transistors***F. Y. Liu, I. Ionica, M. Bawedin, S. Cristoloveanu p.277***Sub-22nm scaling of UTB2SOI devices for Multi- V_T applications***C. Diaz-Llorente, C. Medina-Bailon, C. Sampedro, F. Gamiz, A. Godoy, L. Donetti p.281***Dependence of Spin Lifetime on Spin Injection Orientation in Strained Silicon Films***J. Ghosh, D. Osintsev, V. Sverdlov, S. Selberherr p.285***Determination of ad hoc deposited charge on bare SOI wafers***C. Fernandez, N. Rodriguez, C. Marquez, F. Gamiz p.289***High Temperature Influence on Analog Parameters of Bulk and SOI nFinFETs***A.V Oliveira, P. G. D. Agopian, E. Simoen, C. Claeys, J. A. Martino p.293***Experimental demonstration of planar SiGe on Si TFETs with counter doped pocket***S. Blaeser, S. Richter, S. Wirths, S. Trellenkamp, D. Buca, Q. T. Zhao, S. Mantl p.297***Band structure of III-V thin films: an atomistic study of non-parabolic effects in confinement direction***G. Mugny, F. Triozon, J. Li, Y.-M. Niquet, G. Hiblot, D. Rideau, C. Delerue p.301***SOI/SOS MOSFET Universal Compact SPICE Model with Account for Radiation Effects***K. O. Petrosyants, I. A. Kharitonov, L. M. Sambursky p.305***Systematic study of the palladium-graphene contact***A. Gahoi, V. Passi, S. Kataria, S. Wagner, A. Bablich, M. C. Lemme p.309***Ultra-Low-Power Diodes Using Junctionless Nanowire Transistors***M. de Souza, R. T. Doria, R. Trevisoli, M. A. Pavanello p.313***Impact of Back Plane on the carrier mobility in 28nm UTBB FDSOI devices, for ESD applications***S. Athanasiou, P. Galy, S. Cristoloveanu p.317***Ovonic Materials for Memory Nano-Devices: Stability of I(V) Measurements***M. Rudan, E. Piccinini, F. Buscemi, R. Brunetti p.321*